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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	10/761369	
			Filing Date	January 22, 2004	
			First Named Inventor	Kristy A. Campbell	
			Art Unit	2818	
			Examiner Name	LONG TRAN	
Sheet	1	of	11	Attorney Docket Number	M4065.0988/P988-A

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
✓	AA	2002/0000666		1/3/2002	Kozicki et al.	
	AB	2002/0072188		6/13/2002	Gilton	
	AC	2002/0106849		08/08/2002	Moore	
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Sheet	2	of	11	Attorney Docket Number	M4065.0988/P988-A

✓	AU1	3,622,319	11/1971	Sharp	
	AV1	3,743,847	7/1973	Boland	
	AW1	4,269,935	5/1981	Masters et al.	
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UR	AR3	6,316,784	11/2001	Zahorik et al.	
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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁶ (if known)				
UR	BA	56126916	10/19981	Akira et al.		
	BB	WO 97/48032	12/18/1997	Kozicki et al.		
	BC	WO 99/28914	06/10/1999	Kozicki et al.		
	BD	WO 00/48196	08/17/2000	Kozicki et al.		
	BE	WO 02/21542	03/14/2002	Kozicki et al.		
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	BF	59-20913	2/1984			
	BG	50-18597	9/1973			

Examiner Signature		Date Considered	6/17/05
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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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		Art Unit			
		Examiner Name			
Sheet	4	of	11	Attorney Docket Number	M4065.0988/P988-A

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
W	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, <i>Vacuum</i> 59 (2000) 845-853.	
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, <i>J. Vac. Sci. Technol.</i> 9 (1972) 1182-1189.	
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, <i>Rev. Mod. Phys.</i> 50 (1978) 209-220.	
	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge ₂₅ -xSb _x , <i>Appl. Phys. A</i> 55 (1992) 167-169.	
	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe _{1-x} , <i>Egypt, J. Phys.</i> 17 (1986) 335-342.	
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, <i>Inorganic Materials</i> 23 (1987) 137-139.	
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, <i>Phys. Stat. Sol. (a)</i> 19 (1973) K169-K171.	
	CH	Angell, C.A., Mobile ions in amorphous solids, <i>Annu. Rev. Phys. Chem.</i> 43 (1992) 693-717.	
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, <i>Solid state Ionics</i> 136-137 (2000) 1085-1089.	
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, <i>J. Non-Cryst. Solids</i> 11 (1972) 97-104.	
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, <i>Phys. Rev. Lett.</i> 62 (1989) 808-810	
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	CM	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, <i>J. Chem. Phys.</i> 111 (1999) 7546-7557.	
	CN	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, <i>Solid state Ionics</i> 136-137 (2000) 1025-1029.	
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	CP	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, <i>Phys. Rev. Lett.</i> 73 (1994) 264-267.	
	CQ	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag ₂ Se-M, <i>Thin solid films</i> 70 (1980) L1-L4.	
	CR	Bernede, J.C., Polarized memory switching in MIS thin films, <i>Thin Solid Films</i> 81 (1981) 155-160.	
	CS	Bernede, J.C., Switching and silver movements in Ag ₂ Se thin films, <i>Phys. Stat. Sol. (a)</i> 57 (1980) K101-K104.	
	CT	Bernede, J.C., Commutations dans les couches minces de selenium, <i>Phys. Stat. Vol. (a)</i> , 97-102 (1981).	
	CU	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, <i>Thin solid films</i> 131 (1985) L61-L64.	
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Sheet	5	of	11	Attorney Docket Number	M4065.0988/P988-A

✓	CW	Bernede, J.C.; Khelil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in Al-Al ₂ O ₃ -Ag ₂ -xSe _{1+x} thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.	
	CX	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg ₄ I ₅ , Solid State Ionics 70/71 (1994) 72-76.	
	CY	Boolchand, P., The maximum in glass transition temperature (T _g) near x=1/3 in GexSe _{1-x} Glasses, Asian Journal of Physics (2000) 9, 709-72.	
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	CB1	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.	
	CC1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.	
	CD1	Boolchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe ₂ glass, Phys. Rev. B 25 (1982) 2975-2978.	
	CE1	Boolchand, P.; Grothaus, J.; Phillips, J.C., Broken chemical order and phase separation in GexSe _{1-x} glasses, Solid state comm. 45 (1983) 183-185.	
	CF1	Boolchand, P.; Bresser, W.J., Compositional trends in glass transition temperature (T _g), network connectivity and nanoscale chemical phase separation in chalcogenides, Dept. of ECECS, Univ. Cincinnati (October 28, 1999) 45221-0030.	
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	CH1	Bresser, W.; Boolchand, P.; Suranyi, P., Rigidity percolation and molecular clustering in network glasses, Phys. Rev. Lett. 56 (1986) 2493-2496.	
	CI1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; de Neufville, J.P., Intrinsically broken chalcogen chemical order in stoichiometric glasses, Journal de Physique 42 (1981) C4-193-C4-196.	
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	CK1	Cohen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe ₂ Crystals, Science 258 (1992) 271-274.	
	CL1	Chatterjee, R.; Asokan, S.; Titus, S.S.K., Current-controlled negative-resistance behavior and memory switching in bulk As-Te-Se glasses, J. Phys. D: Appl. Phys. 27 (1994) 2624-2627.	
	CM1	Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy GexSe _{1-x} films, Appl. Phys. Lett. 37 (1980) 1075-1077.	
	CN1	Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936.	
	CO1	Chen, G.; Cheng, J.; Chen, W., Effect of Si ₃ N ₄ on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.	
	CP1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.	
	CQ1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.	
	CR1	Dalven, R.; Gill, R., Electrical properties of beta-Ag ₂ Te and beta-Ag ₂ Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.	
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WRT	CT1	Deamaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.	
	CU1	Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 162-180.	
	CV1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.	
	CW1	Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.	
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	CC2	Elliott, S.R., A unified mechanism for metal photodissolution in amorphous chalcogenide materials, J. Non-Cryst. Solids 130 (1991) 85-97.	
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	CE2	Elsamanoudy, M.M.; Hegab, N.A.; Fadel, M., Conduction mechanism in the pre-switching state of thin films containing Te As Ge Si, Vacuum 46 (1995) 701-707.	
	CF2	El-Zahed, H.; El-Korashy, A., Influence of composition on the electrical and optical properties of Ge ₂₀ BixSe _{80-x} films, Thin Solid Films 376 (2000) 236-240.	
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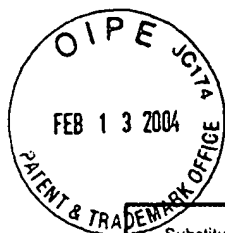
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UK	BA	EP 1 202 285 A2	2/2002	Nishihara et al.		

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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/761,369
				Filing Date	January 22, 2004
				First Named Inventor	Kristy A. Campbell
				Art Unit	N/A 2818
				Examiner Name	Not Yet Assigned LONG PAK
Sheet	1	of	1	Attorney Docket Number	M4065.0988/P988-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number-Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

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UKT	CA	YOJI KAWAMOTO, et al.; "Ionic Conduction in As ₂ S ₃ -Ag ₂ S, GeS ₂ -GeS-Ag ₂ S and P ₂ S ₅ -Ag ₂ S Glasses" Journal of Non-Crystalline Solids 20, 393-404 (1976).	

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Examiner Signature		Date Considered	6/17/05
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